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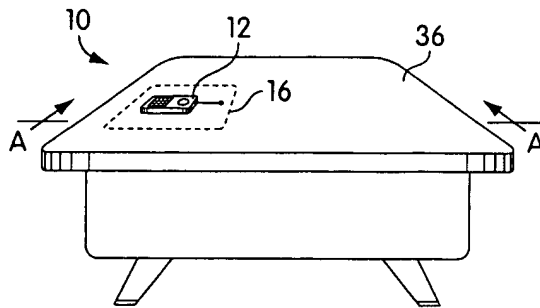


Fig. 1A

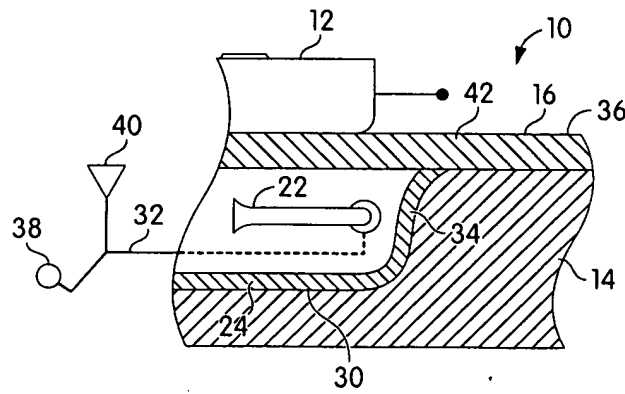
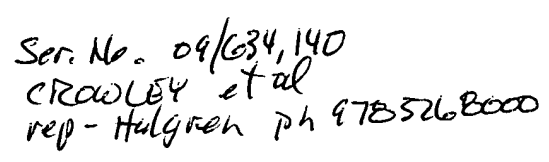


Fig. 1B



A cross-sectional view of a semiconductor device 10. The device consists of a substrate 24 with a top surface 52. A layer 16 is formed on the top surface 52. A layer 54 is formed on top of layer 16. A layer 50 is formed on top of layer 54. A layer 56 is formed on top of layer 50. A layer 56 is formed on top of layer 50.

Fig. 2B

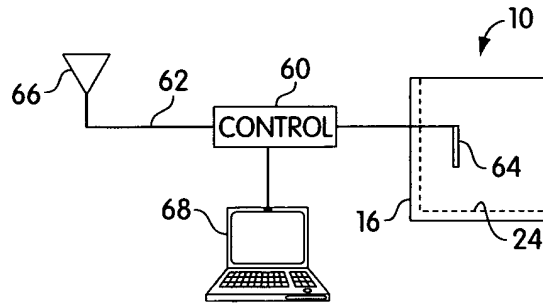
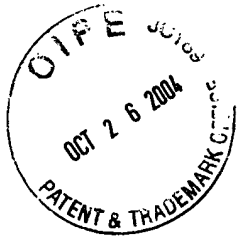


Fig. 3A

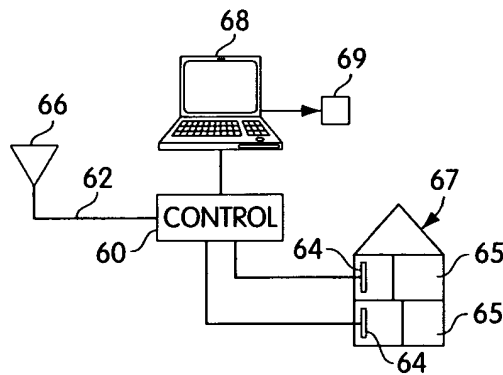


Fig. 3B



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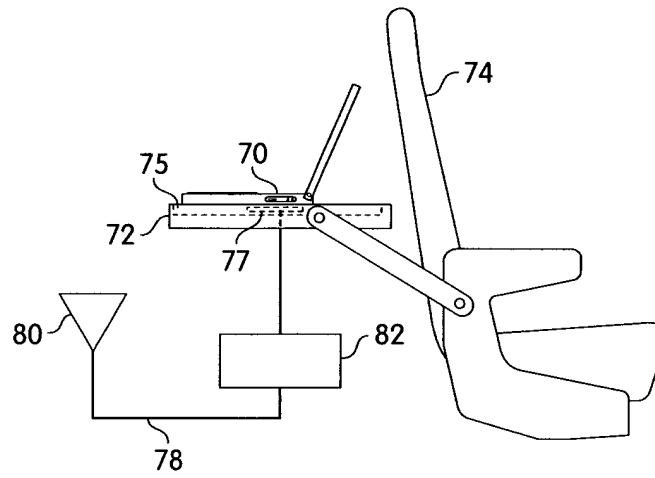


Fig. 4